CMOS 4-Bit Magnitude Comparator

High Voltage Types (20-Volt Rating)

The RCA-CD4585B is a 4-bit magnitude comparator designed for use in computer and logic applications that require the comparison of two 4-bit words. This logic circuit determines whether one 4-bit word (Binary or BCD) is "less than", "equal to", or "greater than" a second 4-bit word.

The CD4585B has eight comparing inputs (A3, B3, through A0, B0), three outputs (A <B,A = B,A > B) and three cascading inputs (A < B, A = B, A > B) that permit systems designers to expand the comparator function to 8, 12, 16.....4N bits. When a single CD4585B is used, the cascading inputs are connected as follows: (A < B) = low, (A = B) = high, (A > B) = high.

Cascading these units for comparison of more than 4 bits is accomplished as shown in Fig. 13.

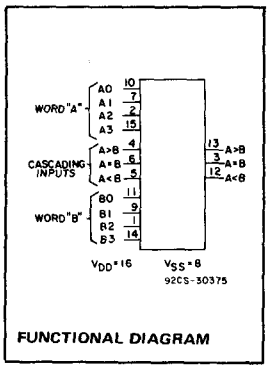
The CD4585B types are supplied in 16-lead hermetic dual-in-line ceramic packages (D and F suffixes), 16-lead dual-in-line plastic packages (E suffix), 16-lead ceramic flat packages (K suffix), and in chip form (H suffix). This device is pin-compatible with low-power TTL type 7485 and the CMOS types MC14585 and 40085.

Features:

- **Expansion to 8,12,16.....4N bits by cascading units**
- **Medium-speed operation:**
  compares two 4-bit words
  in 180 ns (typ.) at 10 V
- **100% tested for quiescent current at 20 V**
- **Standardized symmetrical output characteristics**
- **5-V, 10-V, and 15-V parametric ratings**
- **Maximum input current of 1 μA at 18 V over full package temperature range; 100 nA at 18 V and 25°C**
- **Noise margin (full package temperature range) = 1 V at V_{DD} = 5 V**
  2 V at V_{DD} = 10 V
  2.5 V at V_{DD} = 15 V
- **Meets all requirements of JEDEC Tentative Standard No. 13A, "Standard Specifications for Description of 'B' Series CMOS Devices"**

Applications:

- **Servo motor controls**
- **Process controllers**



FUNCTIONAL DIAGRAM

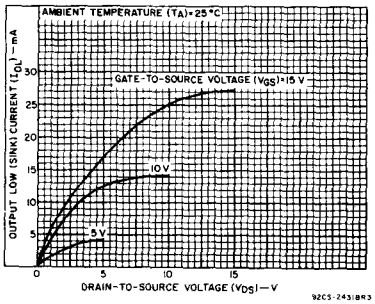


Fig.1 – Typical output low (sink) current characteristics.

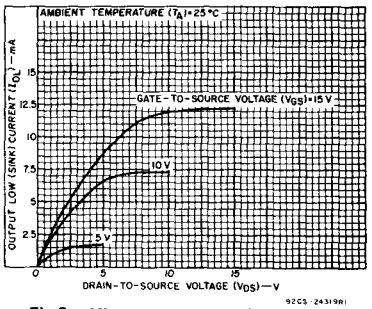


Fig.2 – Minimum output low (sink) current characteristics.

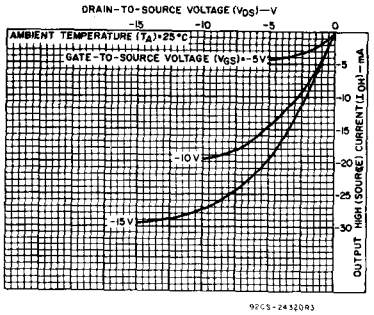


Fig.3 – Typical output high (source) current characteristics.

MAXIMUM RATINGS, *Absolute-Maximum Values:*

DC SUPPLY-VOLTAGE RANGE, (V_{DD}) (*Voltages referenced to V_{SS} Terminal*)	−0.5 to +20 V
INPUT VOLTAGE RANGE, ALL INPUTS	−0.5 to V_{DD} +0.5 V
DC INPUT CURRENT, ANY ONE INPUT	±10 mA
POWER DISSIPATION PER PACKAGE (P_D):	
For T_A = −40 to +60°C (PACKAGE TYPE E)	500 mW
For T_A = +60 to +85°C (PACKAGE TYPE E)	Derate Linearly at 12 mW/°C to 200 mW
For T_A = −55 to +100°C (PACKAGE TYPES D, F, K)	500 mW
For T_A = +100 to +125°C (PACKAGE TYPES D, F, K)	Derate Linearly at 12 mW/°C to 200 mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR	
FOR T_A = FULL PACKAGE-TEMPERATURE RANGE (All Package Types)	100 mW
OPERATING-TEMPERATURE RANGE (T_A):	
PACKAGE TYPES D, F, K, H)	−55 to +125°C
PACKAGE TYPE E	−40 to +85°C
STORAGE TEMPERATURE RANGE (T_{stg})	−65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 ± 1/32 inch (1.59 ± 0.79 mm) from case for 10 s max.	+265°C

RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	Min.	Max.	
Supply-Voltage Range (For T_A = Full Package-Temperature Range)	3	18	V

TRUTH TABLE

INPUTS							OUTPUTS		
COMPARING				CASCADING					
A3, B3	A2, B2	A1, B1	A0, B0	A<B	A=B	A>B	A<B	A=B	A>B
A3>B3	X	X	X	X	X	1	0	0	1
A3=B3	A2>B2	X	X	X	X	1	0	0	1
A3=B3	A2=B2	A1>B1	X	X	X	1	0	0	1
A3=B3	A2=B2	A1=B1	A0>B0	X	X	1	0	0	1
A3=B3	A2=B2	A1=B1	A0=B0	0	0	1	0	0	1
A3=B3	A2=B2	A1=B1	A0=B0	0	1	X	0	1	0
A3=B3	A2=B2	A1=B1	A0=B0	1	0	X	1	0	0
A3=B3	A2=B2	A1=B1	A0<B0	X	X	X	1	0	0
A3=B3	A2=B2	A1<B1	X	X	X	X	1	0	0
A3=B3	A2<B2	X	X	X	X	X	1	0	0
A3<B3	X	X	X	X	X	X	1	0	0

X = Don't Care Logic 1 = High Level Logic 0 = Low Level

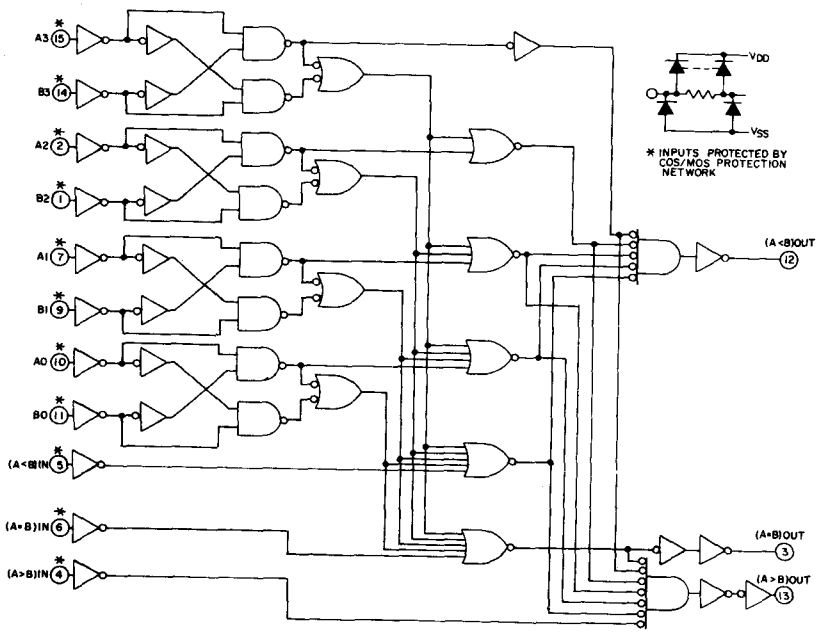


Fig.4 – Logic diagram.

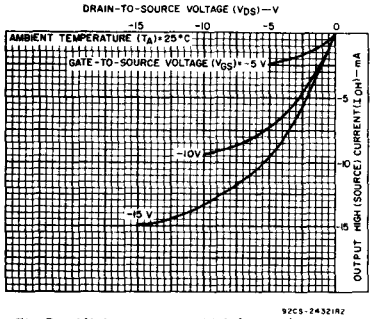


Fig. 5 – Minimum output high (source) current characteristics.

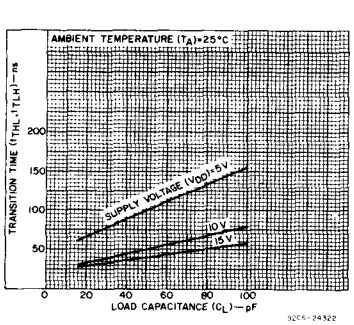


Fig. 6 – Typical transition time as a function of load capacitance.

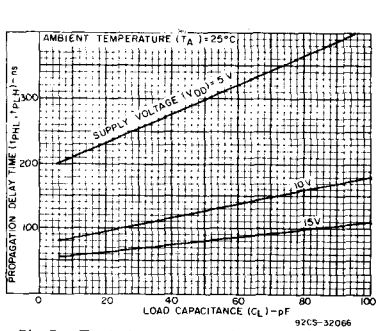


Fig. 7 – Typical propagation delay time ("comparing inputs" to outputs) as a function of load capacitance.

STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C) Values at -55, +25, +125 Apply to D, F, K, H. Packages Values at -40, +25, +85 Apply to E Package							UNITS
								+25			
	V_O (V)	V_{IN} (V)	V_{DD} (V)	-55	-40	+85	+125	Min.	Typ.	Max.	
Quiescent Device Current, I_{DD} Max.	–	0,5	5	5	5	150	150	–	0.04	5	μA
	–	0,10	10	10	10	300	300	–	0.04	10	
	–	0,15	15	20	20	600	600	–	0.04	20	
	–	0,20	20	100	100	3000	3000	–	0.08	100	
Output Low (Sink) Current I_{OL} Min.	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1	–	mA
	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	–	
	1.5	0,15	15	4.2	4	2.8	2.4	3.4	6.8	–	
Output High (Source) Current, I_{OH} Min.	4.6	0,5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	–	
	2.5	0,5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2	–	
	9.5	0,10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	–	
	13.5	0,15	15	-4.2	-4	-2.8	-2.4	-3.4	-6.8	–	
Output Voltage: Low-Level, V_{OL} Max.	–	0,5	5	0.05				–	0	0.05	V
	–	0,10	10	0.05				–	0	0.05	
	–	0,15	15	0.05				–	0	0.05	
Output Voltage: High-Level, V_{OH} Min.	–	0,5	5	4.95				4.95	5	–	
	–	0,10	10	9.95				9.95	10	–	
	–	0,15	15	14.95				14.95	15	–	
Input Low Voltage V_{IL} Max.	0.5,4.5	–	5	1.5				–	–	1.5	V
	1,9	–	10	3				–	–	3	
	1.5,13.5	–	15	4				–	–	4	
Input High Voltage, V_{IH} Min.	0.5,4.5	–	5	3.5				3.5	–	–	
	1,9	–	10	7				7	–	–	
	1.5,13.5	–	15	11				11	–	–	
Input Current I_{IN} Max.	–	0,18	18	±0.1	±0.1	±1	±1	–	$±10^{-5}$	±0.1	μA

DYNAMIC ELECTRICAL CHARACTERISTICS

At T_A = 25°C; Input t_r, t_f = 20 ns, C_L = 50 pF, R_L = 200 kΩ

CHARACTERISTIC	TEST CONDITIONS	V_{DD} Volts	LIMITS Typ.	LIMITS Max.	UNITS
Propagation Delay Time: Comparing Inputs to Outputs, t_{PHL}, t_{PLH}		5	300	600	ns
		10	125	250	
		15	80	160	
Cascading Inputs to Outputs, t_{PHL}, t_{PLH}		5	200	400	
		10	80	160	
		15	60	120	
Transition Time, t_{THL}, t_{TLH}		5	100	200	ns
		10	50	100	
		15	40	80	
Input Capacitance, C_{IN}	Any Input		5	7.5	pF

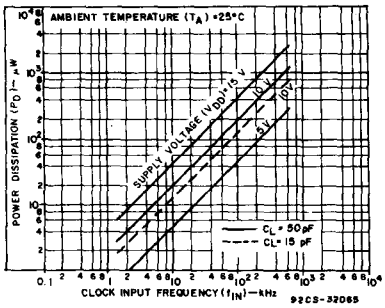


Fig. 8 – Typical dynamic power dissipation as a function of clock input frequency (see Fig. 9–dynamic power dissipation test circuit).

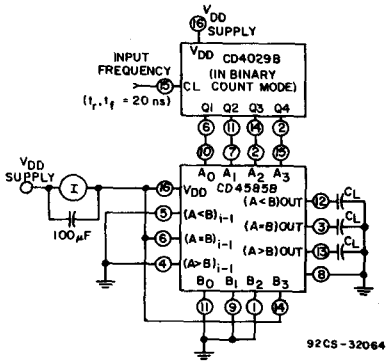


Fig. 9 – Dynamic power dissipation test circuit.

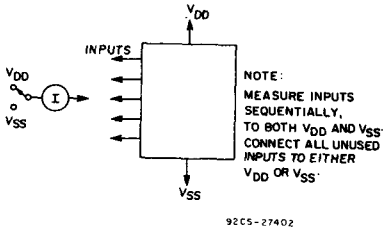


Fig. 10 – Input current test circuit.

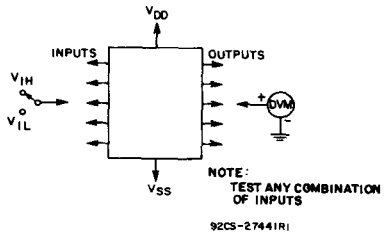


Fig. 11 – Input-voltage test circuit.

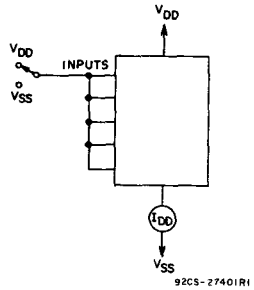


Fig. 12 – Quiescent-device-current test circuit.

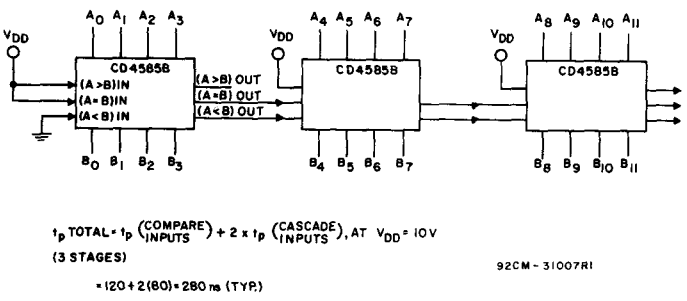
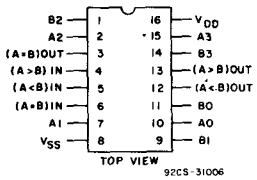
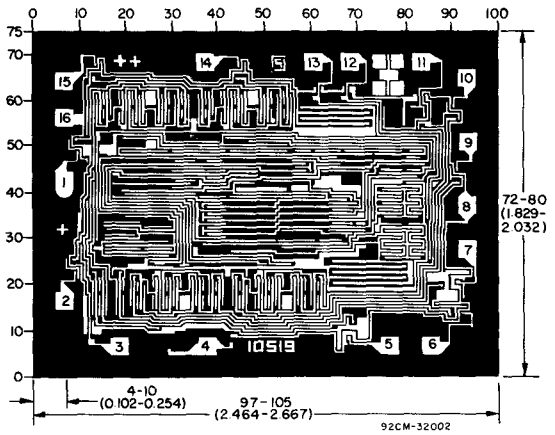


Fig. 13 – Typical speed characteristics of a 12-bit comparator.

TERMINAL ASSIGNMENT





Dimensions and Pad Layout for CD4585BH

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

The photographs and dimensions of each CMOS chip represent a chip when it is part of the wafer. When the wafer is separated into individual chips, the angle of cleavage may vary with respect to the chip face for different chips. The actual dimensions of the isolated chip, therefore, may differ slightly from the nominal dimensions shown. The user should consider a tolerance of −3 mils to +16 mils applicable to the nominal dimensions shown.